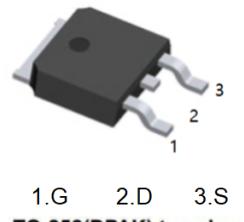
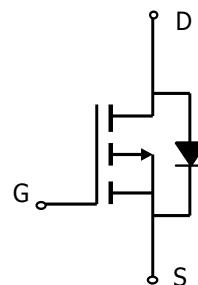


Features

- V_{DS} (V) = -40V
- I_D = -40A
- $R_{DS(ON)} < 22m\Omega$ ($V_{GS} = -10V$)
- $R_{DS(ON)} < 29m\Omega$ ($V_{GS} = -4.5V$)

**General Description**

The AOD4189 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. With the excellent thermal resistance of the TO-252 package, this device is well suited for high current load applications.

**Absolute Maximum Ratings $T_C=25^\circ C$ unless otherwise noted**

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	-40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^{B,H}	I_D	-40	A
$T_C=100^\circ C$		-28	
Pulsed Drain Current ^C	I_{DM}	-50	
Avalanche Current ^C	I_{AR}	-35	
Repetitive avalanche energy $L=0.1mH$ ^C	E_{AR}	61	mJ
Power Dissipation ^B	P_D	62.5	W
$T_C=100^\circ C$		31	
Power Dissipation ^A	P_{DSM}	2.5	
$T_A=70^\circ C$		1.6	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	°C

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^{A,G}	$R_{\theta JA}$	15	20	°C/W
Steady-State		41	50	°C/W
Maximum Junction-to-Case ^{D,F}	$R_{\theta JC}$	2	2.4	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}, V_{GS}=0\text{V}$	-40			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-40\text{V}, V_{GS}=0\text{V}$			-1	μA
			$T_J=55^\circ\text{C}$		-5	
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}= \pm 20\text{V}$			± 100	nA
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	-1.7	-1.9	-3	V
$I_{\text{D(ON)}}$	On state drain current	$V_{GS}=-10\text{V}, V_{DS}=-5\text{V}$	-50			A
$R_{\text{DS(ON)}}$	Static Drain-Source On-Resistance	$V_{GS}=-10\text{V}, I_D=-12\text{A}$		18	22	$\text{m}\Omega$
		$V_{GS}=-4.5\text{V}, I_D=-8\text{A}$		23	29	
g_{FS}	Forward Transconductance	$V_{DS}=-5\text{V}, I_D=-12\text{A}$		35		S
V_{SD}	Diode Forward Voltage	$I_S=-1\text{A}, V_{GS}=0\text{V}$		-0.74	-1	V
I_S	Maximum Body-Diode Continuous Current				-20	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=-20\text{V}, f=1\text{MHz}$		1870		pF
C_{oss}	Output Capacitance			185		pF
C_{rss}	Reverse Transfer Capacitance			155		pF
R_g	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$	2.5	4.5	6.5	Ω
SWITCHING PARAMETERS						
$Q_g(-10\text{V})$	Total Gate Charge	$V_{GS}=-10\text{V}, V_{DS}=-20\text{V}, I_D=-12\text{A}$		31.4	41	nC
$Q_g(-4.5\text{V})$	Total Gate Charge			7.9	10	
Q_{gs}	Gate Source Charge			7.6		nC
Q_{gd}	Gate Drain Charge			6.2		nC
$t_{\text{D(on)}}$	Turn-On Delay Time	$V_{GS}=-10\text{V}, V_{DS}=-20\text{V}, R_L=1.6\Omega, R_{\text{GEN}}=3\Omega$		10		ns
t_r	Turn-On Rise Time			18		ns
$t_{\text{D(off)}}$	Turn-Off Delay Time			38		ns
t_f	Turn-Off Fall Time			24		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=-12\text{A}, dI/dt=100\text{A}/\mu\text{s}$		32	42	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=-12\text{A}, dI/dt=100\text{A}/\mu\text{s}$		30		nC

A: The value of $R_{\theta JA}$ is measured with the device in a still air environment with $T_A=25^\circ\text{C}$. The power dissipation P_{DSM} and current rating I_{DSM} are based on $T_{J(\text{MAX})}=150^\circ\text{C}$, using steady state junction-to-ambient thermal resistance.

B. The power dissipation P_D is based on $T_{J(\text{MAX})}=175^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C: Repetitive rating, pulse width limited by junction temperature $T_{J(\text{MAX})}=175^\circ\text{C}$.

D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using $t \leq 300 \mu\text{s}$ pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(\text{MAX})}=175^\circ\text{C}$. The SOA curve provides a single pulse rating.

G. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$.

H. The maximum current rating is limited by bond-wires.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

P-Channel MOSFET

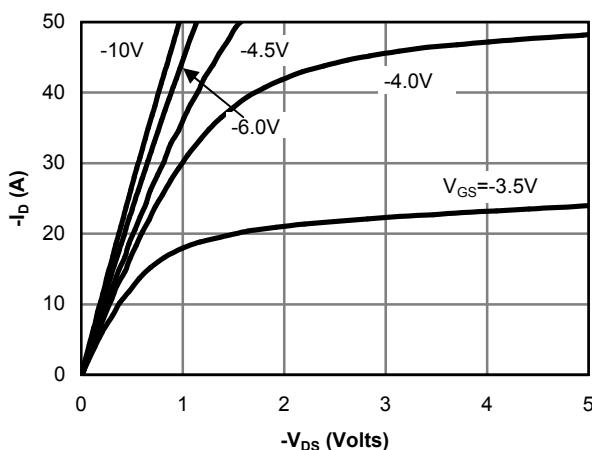


Figure 1: On-Region Characteristics

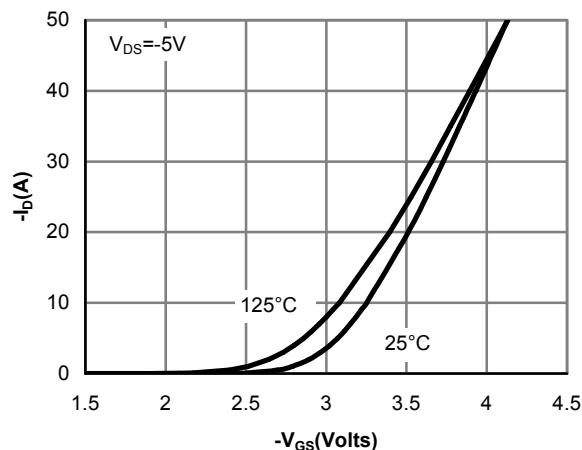


Figure 2: Transfer Characteristics

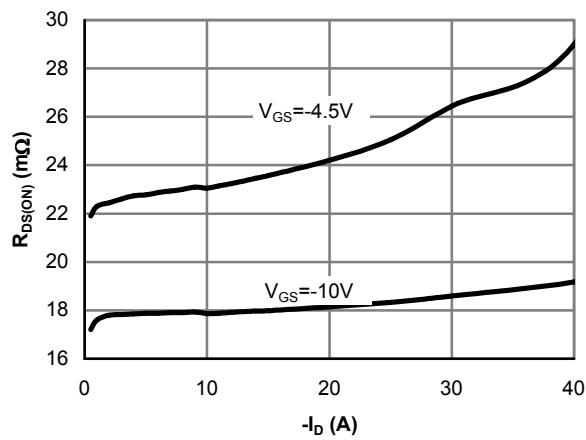


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

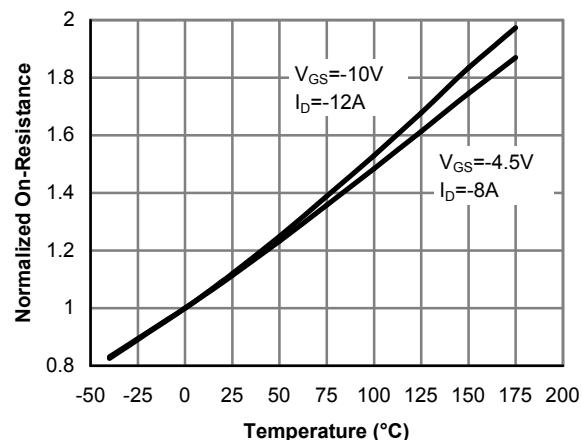


Figure 4: On-Resistance vs. Junction Temperature

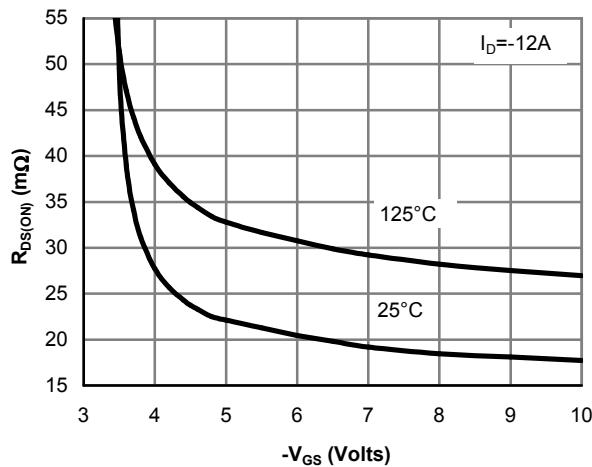


Figure 5: On-Resistance vs. Gate-Source Voltage

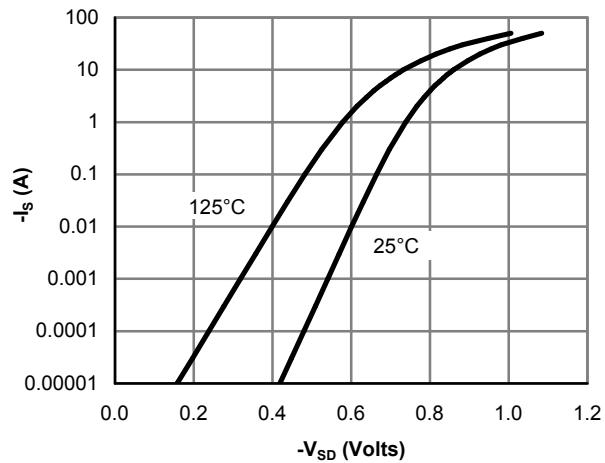


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

P-Channel MOSFET

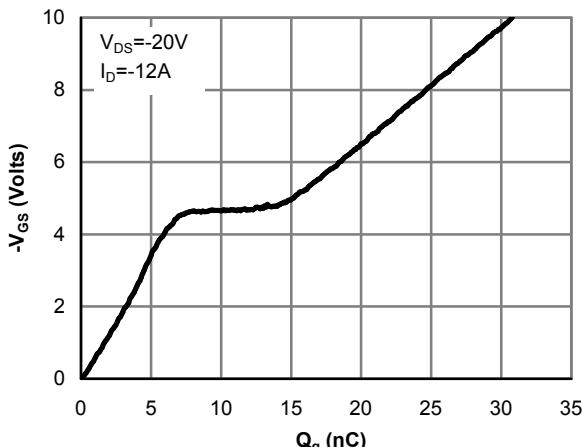


Figure 7: Gate-Charge Characteristics

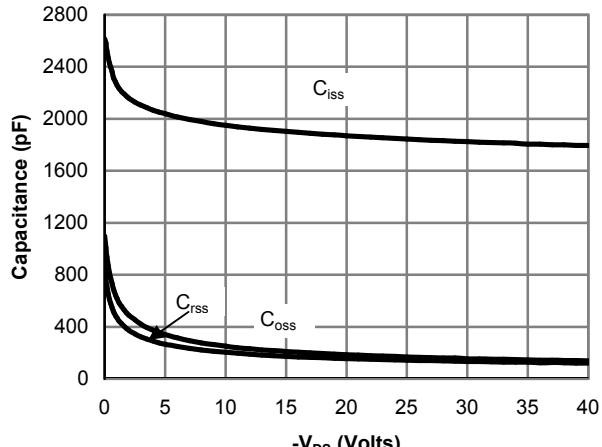


Figure 8: Capacitance Characteristics

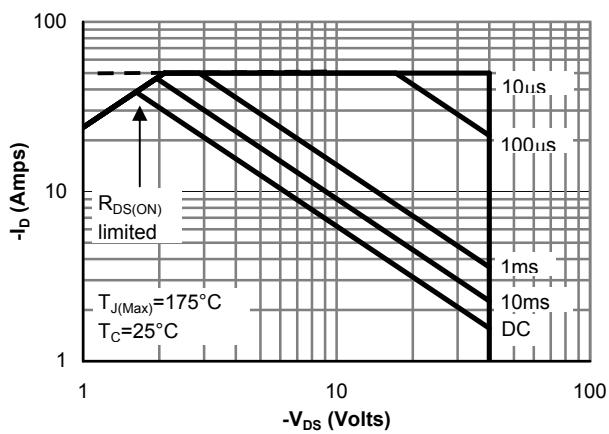


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

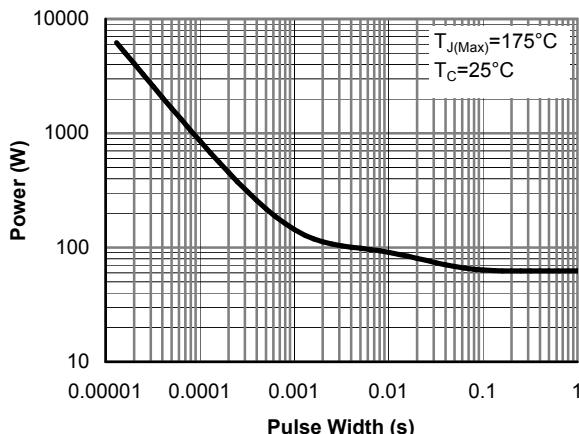


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

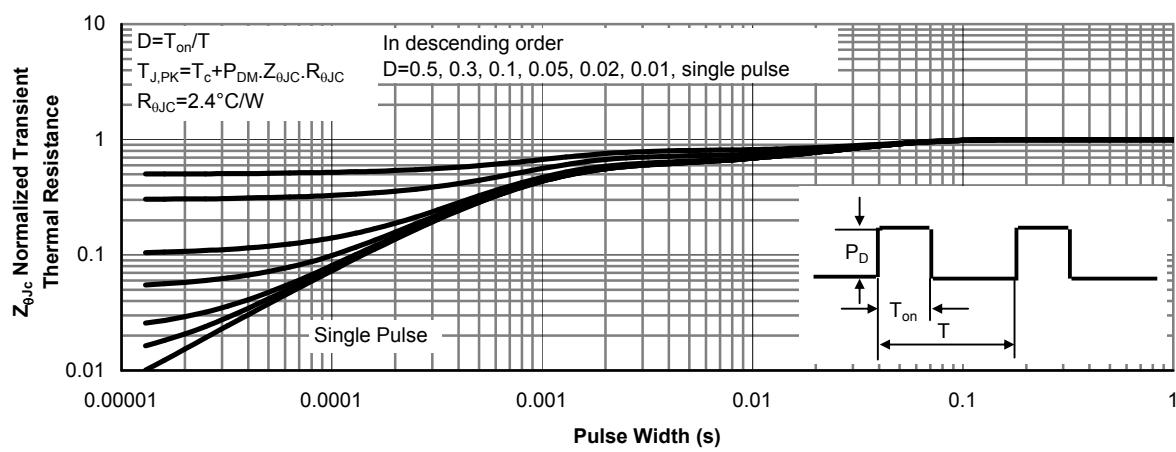


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

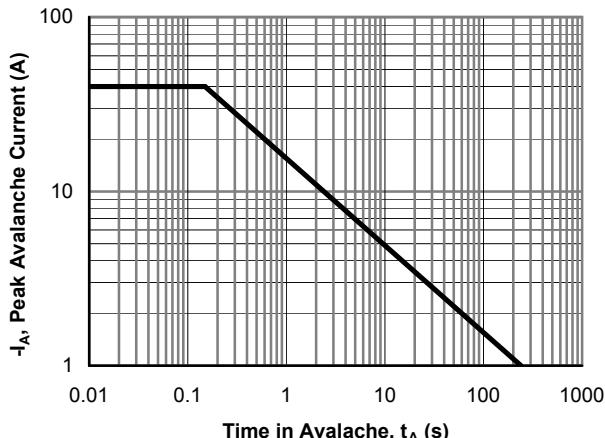


Figure 12: Single Pulse Avalanche Capability

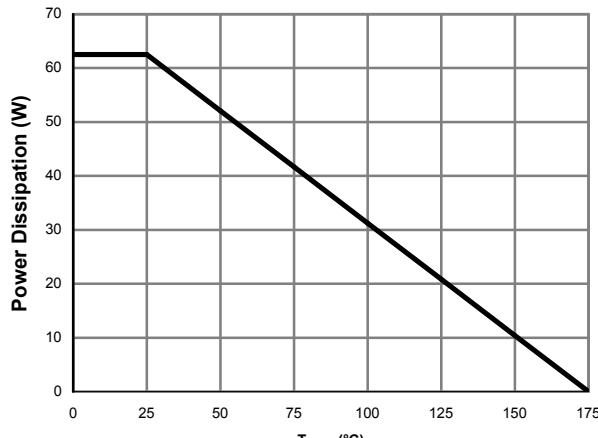


Figure 13: Power De-rating (Note B)

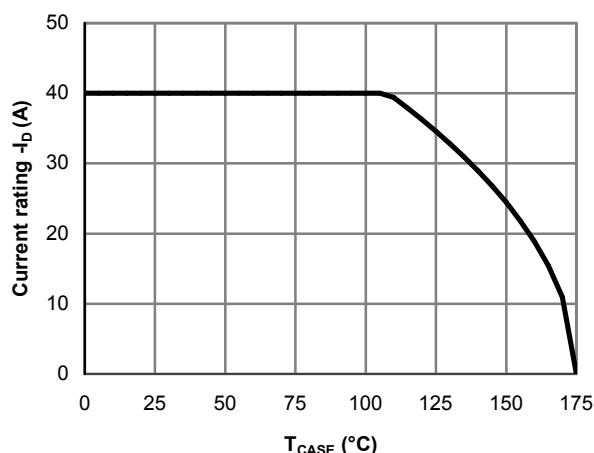


Figure 14: Current De-rating (Note B)

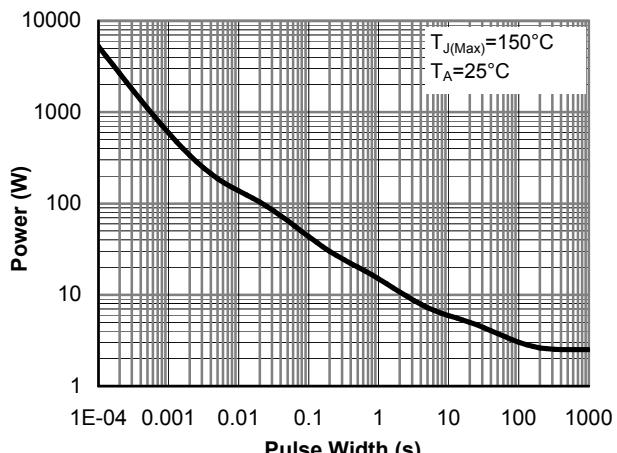


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note G)

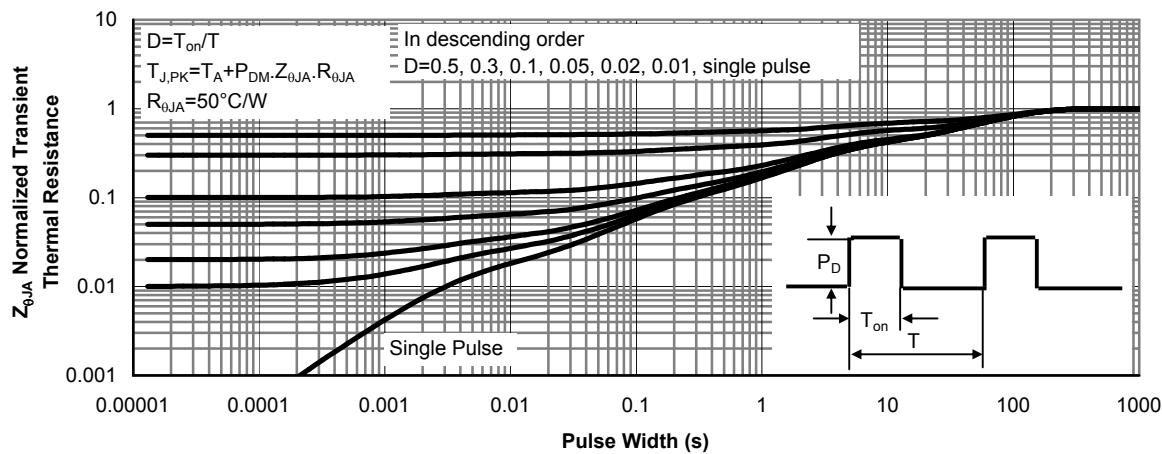
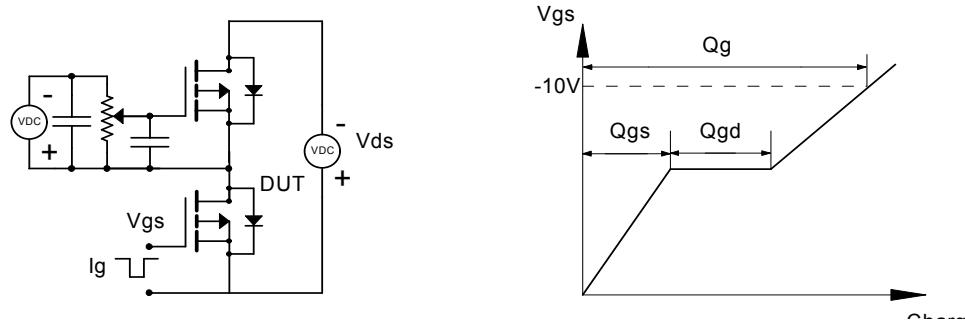
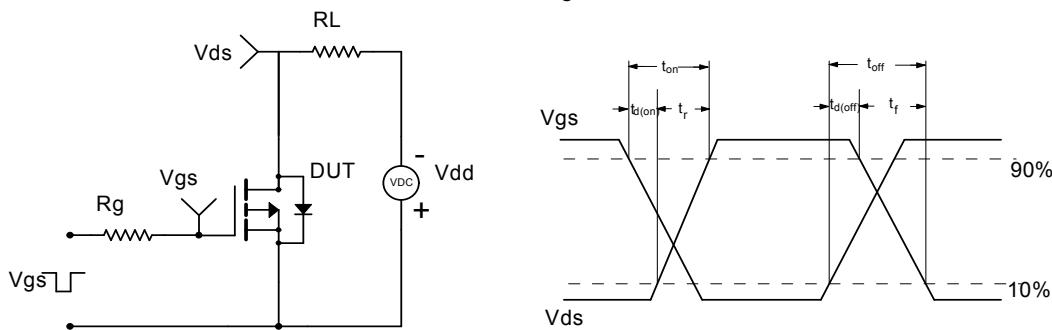


Figure 16: Normalized Maximum Transient Thermal Impedance (Note G)

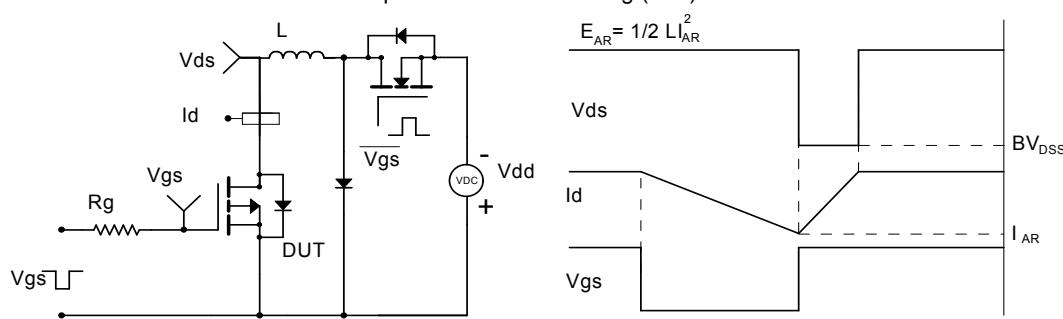
Gate Charge Test Circuit & Waveform



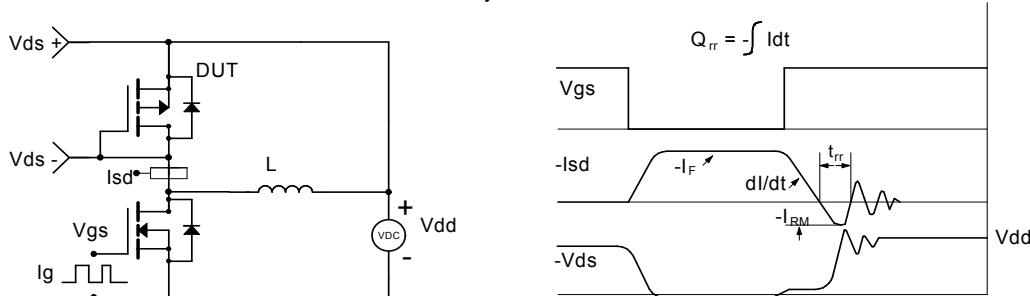
Resistive Switching Test Circuit & Waveforms



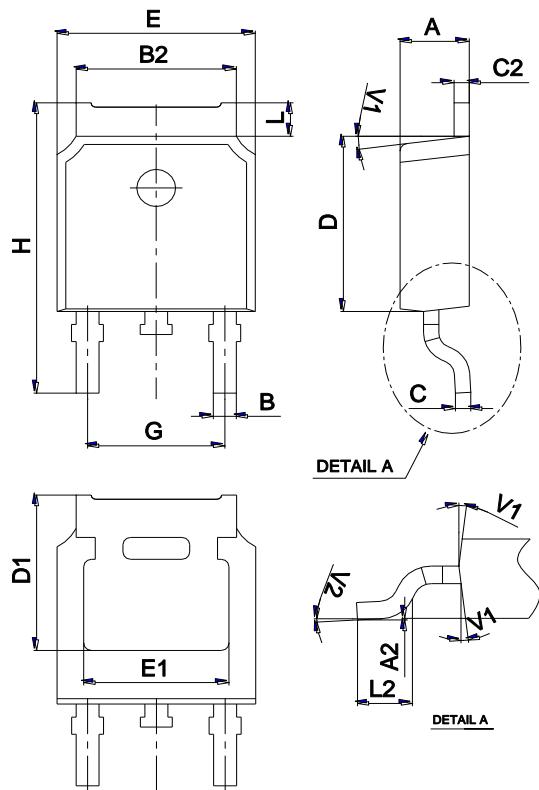
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

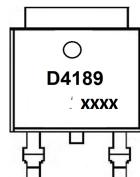


Package Mechanical Data TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
AOD4189	TO-252	2500	Tape and reel